

# Low Power, High Performance RF Transceiver

## **Applications**

- Low power, high performance, wireless systems with 1 to 1000 kbit/s data rate
- 169 / 433 / 868 / 915 / 920 MHz ISM/SRD bands
- Possible support for additional frequency bands:
- 137 160, 205 240 and 274 320 MHz
- Automatic Meter Reading (AMR)
- Home and building automation
- Wireless alarm and security systemsIndustrial monitoring and control
- Industrial monitoring and control
  Wireless healthcare applications
- Wireless heatincare applications
  Wireless sensor networks and Active RFID
- IEEE 802.15.4g applications
- Wireless M-bus, all modes

## Regulations

Suitable for systems targeting compliance with:

Europe	ETSI EN 300 220, EN 54-25
US	FCC CFR47 Part 15
	FCC CFR47 Part 90
Japan	ARIB STD-T30, T67, T108

## **Key Features**

#### **RF Performance and analog features**

- High performance single chip transceiver
  - Excellent receiver sensitivity:
    - -123 dBm at 1.2 kbps
    - -110 dBm at 50 kbps
    - -127 dBm using built-in coding gain
  - Blocking performance: 90 dB at 10 MHz
  - Adjacent channel selectivity: up to 60 dB at 12.5 kHz offset
  - Very low phase noise: -110 dBc/Hz at 10 kHz offset (169 MHz)
- Programmable output power up to +16 dBm with 0.4 dB step size
- Automatic output power ramping
- Supported modulation formats: 2-FSK, 2-GFSK, 4-FSK, 4-GFSK, MSK, OOK
- Supports up to 1 Mbps in transmit and receive

## Description

The **CC1200** is a fully integrated single-chip radio transceiver designed for high performance at very low power and low voltage operation in cost effective wireless systems. All filters are integrated, removing the need for costly external SAW and IF filters. The device is mainly intended for the ISM (Industrial, Scientific and Medical) and SRD (Short Range Device) frequency bands at 164-192 MHz, 410-480 MHz and 820-960 MHz.

The **CC1200** provides extensive hardware support for packet handling, data buffering, burst transmissions, clear channel assessment, link quality indication and Wake-On-Radio. The **CC1200** main operating parameters can be controlled via an SPI interface. In a typical system, the **CC1200** will be used together with a microcontroller and only few external passive components.

#### Low current consumption:

- Enhanced Wake-On-Radio functionality for automatic low-power receive polling
- Power down: 0.3 µA
  - RX: 2 mA in RX Sniff Mode
  - RX: 17 mA peak current in low power mode
  - RX: 23 mA peak current in high performance mode
  - TX: 45 mA at +14 dBm

#### **Digital features**

- WaveMatch: Advanced digital signal processing for improved sync detect performance
- Security: Hardware AES128 accelerator
- Data FIFOs: separate 128-byte RX and TX
- Includes functions for antenna diversity support
- Support for re-transmissions
- Support for auto-acknowledge of received packets
- Automatic Clear Channel Assessment (CCA) for listenbefore-talk (LBT) systems
- Built in coding gain support for increased range and robustness
- Digital RSSI measurement
- Support for seamless integration with the **CC1190** for increased range giving up to 3 dB improvement in sensitivity and up to +27 dBm output power
- Improved OOK shaping for less occupied bandwidth, enabling higher output power whilst meeting regulatory requirements

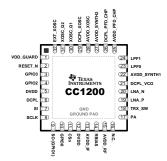
#### Dedicated packet handling for 802.15.4g

- CRC 16/32
- FEC, dual sync detection (FEC and non FEC packets)
- Whitening

#### General

- RoHS compliant 5x5mm QFN 32 package
- Pin compatible with the CC1120

The **CC1200** and the **CC1120** are both part of the high performance transceiver family. The **CC1120** is more optimized towards narrowband applications, while the **CC1200** is optimized towards wideband applications but can also cover narrowband down to 12.5 kHz channels well.





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## **1** Electrical Specifications

All measurements performed on CC1200EM\_868\_930 rev.1.0.0, CC1200EM\_420\_470 rev.1.0.1 or CC1200EM\_169 rev.1.2

### 1.1 Absolute Max Ratings

Parameter	Min	Тур	Max	Unit	Condition
Supply Voltage ("VDD")	-0.3		3.9	V	
Storage Temperature Range	-40		125	°C	
ESD			2000	V	HBM
ESD			500	V	CDM
Input RF level			+10	dBm	
Voltage on Any Digital Pin	-0.3		VDD+0.3	V	
			max 3.9	-	
Voltage on Analog Pins (including "DCPL" pins)	-0.3		2.0	V	

### 1.2 General Characteristics

Parameter	Min	Тур	Max	Unit	Condition
Voltage Supply Range	2.0		3.6	V	
Temperature Range	-40		85	°C	

### 1.3 **RF Characteristics**

Parameter	Min	Тур	Max	Unit	Condition
	820		960	MHz	
	410		480	MHz	
Frequency Bands	164		192	MHz	
	(274)		(320)	MHz	Please contact TI for more
	(205)		(240)	MHz	information about the use of these frequency bands
	(137)		(160)	MHz	
		30		Hz	In 820-960 MHz band
Frequency Resolution		15		Hz	In 410-480 MHz band
		6		Hz	In 164-192 MHz band
Datarate	0		1000	kbps	Packet mode
	0		500	kbps	Transparent mode
Datarate Step Size		1 ppm		bps	





### 1.4 Regulatory Standards

Performance Mode	Frequency Band	Suitable for compliance with	Comments		
		ARIB T-108			
		ETSI EN 300 220 category 2			
		ETSI EN 54-25	Performance also suitable for systems		
	820 – 960 MHz	FCC PART 15.247	targeting maximum allowed output power in the respective bands, using a		
		FCC PART 15.249	range extender such as the <b>CC1190</b>		
		FCC PART 90 MASK G			
		FCC PART 90 MASK J			
High Performance Mode		ARIB T-67			
	410 – 480 MHz	ARIB RCR STD-30	Performance also suitable for systems		
		ETSI EN 300 220 category 2	targeting maximum allowed output power in the respective bands, using a range extender		
		FCC PART 90 MASK D			
		FCC PART 90 MASK G			
		ETSI EN 300 220 category 1	Performance also suitable for systems targeting maximum allowed output		
	164 – 192 MHz	FCC PART 90 MASK D	power in the respective bands, using a range extender		
		ETSI EN 300 220 category 2			
	820 – 960 MHz	FCC PART 15.247			
Low Power Mode		FCC PART 15.249			
	410 – 480 MHz	ETSI EN 300 220 category 2			
	164 – 192 MHz	ETSI EN 300 220 category 2			





### 1.5 Current Consumption, Static Modes

 $T_A = 25^{\circ}C$ , VDD = 3.0 V if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
Power Down with Retention		0.3	1	μA	
		0.5		μΑ	Low-power RC oscillator running
XOFF Mode		170		μA	Crystal oscillator / TCXO disabled
IDLE Mode		1.3		mA	Clock running, system waiting with no radio activity

### 1.6 Current Consumption, Transmit Modes

### 868/915/920 MHz bands (High Performance Mode)

 $T_A = 25^{\circ}C$ , VDD = 3.0 V if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
TX Current Consumption +14 dBm		45		mA	
TX Current Consumption +10 dBm		34		mA	

### 433 MHz band (High Performance Mode)

 $T_A = 25^{\circ}C$ , VDD = 3.0 V if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
TX Current Consumption +15 dBm		50		mA	
TX Current Consumption +14 dBm		45		mA	
TX Current Consumption +10 dBm		34		mA	

### 169 MHz band (High Performance Mode)

 $T_{\text{A}}$  = 25°C, VDD = 3.0 V if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
TX Current Consumption +15 dBm		54		mA	
TX Current Consumption +14 dBm		49		mA	
TX Current Consumption +10 dBm		41		mA	

### Low Power Mode

 $T_{\text{A}}$  = 25°C, VDD = 3.0 V,  $f_{\text{c}}$  = 869.5 MHz if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
TX Current Consumption +10 dBm		32		mA	



### 1.7 Current Consumption, Receive Modes

### **High Performance Mode**

 $T_{\text{A}}$  = 25°C, VDD = 3.0 V,  $f_{\text{c}}$  = 869.5 MHz if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
RX Wait for Sync 1.2 kbps, 4 Byte Preamble		2		mA	Using RX Sniff Mode, where the receiver wakes up at regular intervals to look for an incoming
38.4kbps, 4 Byte Preamble		13.4		mA	packet
RX Peak Current 1.2kbps		23		mA	Peak current consumption during packet reception
Average Current Consumption Check for Data Packet Every 1 Second Using Wake on Radio		15		uA	50 kbps, 5 byte preamble, 32 kHz RC oscillator used as sleep timer

### Low Power Mode

 $T_{\text{A}}$  = 25°C, VDD = 3.0 V,  $f_{\text{c}}$  = 869.5 MHz if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
RX Peak Current Low power RX mode 1.2 kbps		17		mA	Peak current consumption during packet reception at the sensitivity level

## **1.8** Receive Parameters<sup>1</sup>

### **General Receive Parameters (High Performance Mode)**

 $T_A = 25^{\circ}C$ , VDD = 3.0 V,  $f_c = 869.5$  MHz if nothing else stated

Parameter	Min	Тур	Мах	Unit	Condition
Saturation		+10		dBm	
Digital Channel Filter Programmable Bandwidth	9.5		1600	kHz	
IIP3, Normal Mode		-14		dBm	At maximum gain
IIP3, High Linearity Mode		-8		dBm	Using 6 dB gain reduction in front end
		±12		%	With carrier sense detection enabled
Datarate Offset Tolerance		±2		%	With carrier sense detection disabled
		±0.2		%	Using WaveWatch (< 4 bit preamble)
Spurious Emissions					Radiated emissions measured
1 - 13 GHz (VCO leakage at 3.5 GHz)		-56		dBm	according to ETSI EN 300 220, $f_c =$
30 MHz to 1 GHz		< -57		dBm	869.5 MHz
Optimum Source Impedance					
868 / 915 / 920 MHz bands	60 + j60 / 30+j30		Ω	(Differential / Single Ended RX	
433 MHz band 169 MHz band		⊦ j60 / 50+ - j40 / 70 -		Ω Ω	Configurations)
	140 4	- j40770	+ j20	32	

 $^{1}$  All RX measurements made at the antenna connector, to a bit error rate limit of 1%



### RX performance in 868/915/920 MHz bands (High Performance Mode)

 $T_A = 25^{\circ}C$ , VDD = 3.0 V if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
		-127		dBm	300 bps with coding gain (using a PN spreading sequence with 4 chips per databit) DEV=4 kHz CHF=10 kHz
		-122		dBm	1.2 kbps 2FSK, DEV=4 kHz CHF=11 kHz
		-118		dBm	1.2 kbps 2FSK, DEV=20 kHz CHF=50 kHz
		-113		dBm	4.8 kbps OOK
		-108		dBm	32.768 kbps WMBUS mode S
Sensitivity		-110		dBm	38.4 kbps 2GFSK, DEV=20 kHz CHF=104 kHz
		-109		dBm	50 kbps 2GFSK, DEV=25 kHz, CHF=104 kHz
		-107		dBm	100 kbps 2GFSK, DEV=50kHz, CHF=208 kHz
		-103		dBm	200 kbps 2GFSK, DEV=50kHz, CHF=416 kHz
		-97		dBm	500 kbps 2GFSK, CHF=833 kHz, MSK
		-97		dBm	1 Mbps 4GFSK, DEV=400 kHz, CHF=1.66 MHz
Blocking and Selectivity		54		dB	± 12.5 kHz (adjacent channel)
1.2 kbps 2FSK, 12.5 kHz channel		55		dB	± 25 kHz (alternate channel)
separation, 4 kHz deviation, 11 kHz channel filter		77		dB	± 2 MHz
		82		dB	± 10 MHz
Blocking and Selectivity		47		dB	± 50 kHz (adjacent channel)
1.2 kbps 2FSK, 50 kHz channel		49		dB	+ 100 kHz (alternate channel)
separation, 20 kHz deviation, 50 kHz channel filter		74		dB	± 2 MHz
		81		dB	± 10 MHz
		39		dB	± 200 kHz
Blocking and Selectivity		46		dB	± 400 kHz
32.768 kbps WMBUS mode S		66		dB	± 2 MHz
		70		dB	± 10 MHz
Blocking and Selectivity		44		dB	+ 100 kHz (adjacent channel)
38.4 kbps 2GFSK, 100 kHz channel		44		dB	± 200 kHz (alternate channel)
separation, 20 kHz deviation, 104 kHz		64		dB	± 2 MHz
channel filter		71		dB	± 10 MHz
Blocking and Selectivity		41		dB	± 200 kHz (adjacent channel)
50 kbps 2GFSK, 200 kHz channel		46		dB	± 400 kHz (alternate channel)
separation, 25 kHz deviation, 104 kHz channel filter		66		dB	± 2 MHz
(Same modulation format as 802.15.4g Mandatory Mode)		71		dB	± 10 MHz



Parameter (cont. from prev. page)	Min	Тур	Max	Unit	Condition
		45		dB	± 400 kHz (adjacent channel)
Blocking and Selectivity		54		dB	± 800 kHz (alternate channel)
100 kbps 2GFSK, 50 kHz deviation, 208 kHz channel filter		63		dB	± 2 MHz
		68		dB	± 10 MHz
Blocking and Selectivity		42		dB	+ 1 MHz (adjacent channel)
500 kbps GMSK,		42		dB	± 2 MHz (alternate channel)
833 kHz channel filter		57		dB	± 10 MHz
Blocking and Selectivity		46		dB	± 2 MHz (adjacent channel)
1 Mbps 4GFSK, 400kHz deviation,		52		dB	± 4 MHz (alternate channel)
1.6MHz channel filter		59		dB	± 10 MHz
Image Rejection (Image compensation enabled)		55		dB	1.2 kbps, DEV=4 kHz, CHF=10 kHz, image at -125 kHz

### RX performance in 433 MHz band (High Performance Mode)

 $T_A = 25^{\circ}C$ , VDD = 3.0 V if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
		-123		dBm	1.2 kbps 2FSK, DEV=4 kHz CHF=11 kHz
Sensitivity		-110		dBm	50 kbps 2GFSK, DEV=25 kHz, CHF=119 kHz
		-118		dBm	1.2 kbps 2FSK, DEV=20 kHz CHF=50 kHz
Blocking and Selectivity		60		dB	± 12.5 kHz (adjacent channel)
1.2 kbps 2FSK, 12.5 kHz channel		60		dB	± 25 kHz (alternate channel)
separation, 4 kHz deviation, 11 kHz channel filter		82		dB	± 2 MHz
		90		dB	± 10 MHz
Blocking and Selectivity		53		dB	± 50 kHz (adjacent channel)
1.2 kbps 2FSK, 50 kHz channel		55		dB	+ 100 kHz (alternate channel)
separation, 20 kHz deviation, 50 kHz channel filter		78		dB	± 2 MHz
		85		dB	± 10 MHz
Blocking and Selectivity		48		dB	+ 100 kHz (adjacent channel)
38.4 kbps 2GFSK, 100 kHz channel		48		dB	± 200 kHz (alternate channel)
separation, 20 kHz deviation, 119 kHz channel filter		69		dB	± 2 MHz
		78		dB	± 10 MHz



### RX performance in 169 MHz band (High Performance Mode)

 $T_A = 25^{\circ}C$ , VDD = 3.0 V if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
Sensitivity		-123		dBm	1.2 kbps 2FSK, DEV=4 kHz CHF=11 kHz
Contracting		-118		dbm	1.2 kbps 2FSK, DEV=20 kHz CHF=50 kHz
Blocking and Selectivity		60		dB	± 12.5 kHz (adjacent channel)
1.2 kbps 2FSK, 12.5 kHz channel		60		dB	± 25 kHz (alternate channel)
separation, 4 kHz deviation, 11 kHz channel filter		83		dB	± 2 MHz
channel inter		89		dB	± 10 MHz
Blocking and Selectivity		55		dB	± 50 kHz (adjacent channel)
1.2 kbps 2FSK, 50 kHz channel		55		dB	+ 100 kHz (alternate channel)
separation, 20 kHz deviation, 50 kHz channel filter		77		dB	± 2 MHz
channel inter		83		dB	± 10 MHz
Spurious Response Rejection					
1.2 kbps 2FSK, 12.5 kHz channel separation, 4 kHz deviation, 11 kHz channel filter		60		dB	
Image Rejection (Image compensation enabled)		66		dB	1.2 kbps, DEV=4 kHz, CHF=10 kHz, image at -125 kHz

### **RX performance in Low Power Mode**

 $T_A = 25^{\circ}C$ , VDD = 3.0 V,  $f_c = 869.5$  MHz if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
Sensitivity		-111		dBm	1.2 kbps 2FSK, DEV=4 kHz CHF=11 kHz
		-99		dBm	50 kbps 2GFSK, DEV=25 kHz, CHF=119 kHz
Blocking and Selectivity		47		dB	± 12.5 kHz (adjacent channel)
1.2 kbps 2FSK, 12.5 kHz channel		47		dB	± 25 kHz (alternate channel)
separation, 4 kHz deviation, 11 kHz channel filter (min. PLL loop bandwidth)		77		dB	± 2 MHz
		80		dB	± 10 MHz
Blocking and Selectivity		40		dB	+ 200 kHz (adjacent channel)
50 kbps 2GFSK, 200 kHz channel separation, 25 kHz deviation, 119 kHz		45		dB	+ 400 kHz (alternate channel)
channel filter		64		dB	± 2 MHz
(Same modulation format as 802.15.4g Mandatory Mode)		67		dB	± 10 MHz
Saturation		+10		dBm	



## 1.9 Transmit Parameters

 $T_{\text{A}}\,{=}\,25^{\circ}\text{C},\,\text{VDD}\,{=}\,3.0$  V,  $f_{\text{c}}\,{=}\,869.5$  MHz if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
		+14		dBm	At 915/920 MHz
		+15		dBm	At 915/920 MHz with VDD = 3.6 V
		+15		dBm	At 868 MHz
Max Output Power		+16		dBm	At 868 MHz with VDD = 3.6 V
		+15		dBm	At 433 MHz
		+16		dBm	At 433 MHz with VDD = 3.6 V
		+15		dBm	At 169 MHz
		+16		dBm	At 169 MHz with VDD = 3.6 V
Min Onderst Damag		-11		dBm	Within fine step size range
Min Output Power		-40		dBm	Within coarse step size range
Output Power Step Size		0.4		dB	Within fine step size range
Adjacent Channel Power		-58		dBc	4GFSK 9.6 kbps in 12.5 kHz channel, measured in 8.75 kHz bandwidth (ETSI 300 220 compliant)
Spurious Emissions		00		JD	
(Not including harmonics)		< -60		dBm	
Harmonics 2nd Harm, 169 MHz 2nd Harm, 169 MHz 2nd Harm, 433 MHz 3rd Harm, 433 MHz 2nd Harm, 450 MHz 2nd Harm, 450 MHz 2nd Harm, 868 MHz 3rd Harm, 915 MHz 3rd Harm, 915 MHz 4 <sup>th</sup> Harm, 920 MHz 4 <sup>th</sup> Harm, 920 MHz 4 <sup>th</sup> Harm, 920 MHz		-39 -58 -56 -51 -60 -45 -40 -42 56 52 60 -39 -43 -35		dBm dBm dBm dBm dBm dBwV/m dBuV/m dBuV/m dBuV/m dBm dBm dBm	Transmission at +14 dBm (or maximum allowed in applicable band where this is less than +14 dBm) using TI reference design Emissions measured according to ARIB T-108 in 920 MHz band, ETSI EN 300-220 in 169, 433 and 868 MHz bands and FCC part 15.247 in 450 and 915 MHz band Fourth harmonic in 915 MHz band will require extra filtering to meet FCC requirements if transmitting for long intervals (>50 ms periods)
Optimum Load Impedance 868 / 915 / 920 MHz bands 433 MHz band 169 MHz band		35 + j35 55 + j25 80 + j0		Ω Ω Ω	



## 1.10 PLL Parameters

### **High Performance Mode**

 $T_A = 25^{\circ}C$ , VDD = 3.0 V if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
		-98		dBc/Hz	± 10 kHz offset
Phase Noise in 868/915/920 MHz Bands		-98		dBc/Hz	± 100 kHz offset
		-122		dBc/Hz	± 1 MHz offset
		-104		dBc/Hz	± 10 kHz offset
Phase Noise in 433 MHz Band		-104		dBc/Hz	± 100 kHz offset
		-128		dBc/Hz	± 1 MHz offset
		-110		dBc/Hz	± 10 kHz offset
Phase Noise in 169 MHz Band		-110		dBc/Hz	± 100 kHz offset
		-134		dBc/Hz	± 1 MHz offset

### Low Power Mode

 $T_A = 25^{\circ}C$ , VDD = 3.0 V if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
		-95		dBc/Hz	± 10 kHz offset
Phase Noise in 868/915/920 MHz Bands		-95		dBc/Hz	± 100 kHz offset
		-122		dBc/Hz	± 1 MHz offset
		-101		dBc/Hz	± 10 kHz offset
Phase Noise in 433 MHz Band		-101		dBc/Hz	± 100 kHz offset
		-128		dBc/Hz	± 1 MHz offset
Phase Noise in 169 MHz Band		-107		dBc/Hz	± 10 kHz offset
		-107		dBc/Hz	± 100 kHz offset
		-134		dBc/Hz	± 1 MHz offset



### 1.11 Wake-up and Timing

 $T_{\text{A}}$  = 25°C, VDD = 3.0 V,  $f_{\text{c}}$  = 869.5 MHz if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
Powerdown to IDLE		0.3		ms	Depends on crystal
IDLE to RX/TX		133		μs	Calibration disabled
		369		μs	Calibration enabled
RX/TX Turnaround		43		μs	
RX to RX turnaround <sup>2</sup>		369		μs	With PLL calibration
		0		μs	Without PLL calibration
TX to TX turnaround		369		μs	With PLL calibration
		0		μs	Without PLL calibration
RX/TX to IDLE time		237		μs	Calibrate when leaving RX/TX enabled
		0		μs	Calibrate when leaving RX/TX disabled
Frequency Synthesizer Calibration		0.3		ms	When using SCAL strobe
Minimum Required Number of Preamble Bytes		0.5		bytes	Required for RF front end gain settling only. Digital demodulation does not require preamble for settling
Time From Start RX Until Valid RSSI		4.2		ms	12.5 kHz channels
Including gain settling (function of channel bandwidth. Programmable for trade-off between speed and accuracy)		0.25		ms	120 kHz channels

### 1.12 40 MHz Crystal Oscillator

 $T_A = 25^{\circ}C$ , VDD = 3.0 V if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
Crystal Frequency	38.4		40	MHz	Note: It is recommended that the crystal frequency is chosen so that the RF channel(s) are >1 MHz away from multiples of XOSC in TX and XOSC/2 in RX
Load Capacitance (C <sub>L</sub> )		10		pF	
ESR			60	Ω	Simulated over operating conditions
Start-up Time		0.4		ms	Depends on crystal

### 1.13 40 MHz Clock Input (TCXO)

 $T_A = 25^{\circ}C$ , VDD = 3.0 V if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
Clock Frequency	38.4		40	MHz	
Clock input amplitude (peak-to-peak)	0.8		VDD	V	Simulated over operating conditions

 $<sup>^{2}</sup>$  The turnaround behaviour to and from RX/TX is highly configurable, and the time it takes will depend on how the device is set up. Please see the **CC120X** user guide for more information.



### 1.14 32 kHz Clock Input

 $T_A = 25^{\circ}C$ , VDD = 3.0 V if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
Clock Frequency		32		kHz	
32 kHz Clock Input Pin Input High Voltage	0.8×VDD			V	
32 kHz Clock Input Pin Input Low Voltage			0.2×VDD	V	

### 1.15 40 kHz RC Oscillator

 $T_A = 25^{\circ}C$ , VDD = 3.0 V if nothing else stated.

Parameter	Min	Тур	Max	Unit	Condition
Frequency		40		kHz	After Calibration
Frequency Accuracy After Calibration		±0.1		%	Relative to frequency reference (i.e. 40 MHz crystal or TCXO)
Initial Calibration Time		1.6		ms	

### 1.16 I/O and Reset

 $T_A = 25^{\circ}C$ , VDD = 3.0 V if nothing else stated

Parameter	Min	Тур	Max	Unit	Condition
Logic Input High Voltage	0.8×VDD			V	
Logic Input Low Voltage			0.2×VDD	V	
Logic Output High Voltage	0.8×VDD			V	
Logic Output Low Voltage			0.2×VDD	V	At 4 mA output load or less
Power-on Reset Threshold		1.3		V	Voltage on DVDD pin

### 1.17 Temperature Sensor

 $T_A = 25^{\circ}C$ , VDD = 3.0 V if nothing else stated

Parameter	Min	Тур	Мах	Unit	Condition
Temperature Sensor Range	-40		85	°C	
Temperature Coefficient		2.66		mV / °C	Change in sensor output voltage vs change in temperature
Typical Output Voltage		794		mV	Typical sensor output voltage at $T_A = 25^{\circ}C$ , VDD = 3.0 V
VDD Coefficient		1.17		mV / V	Change in sensor output voltage vs change in VDD

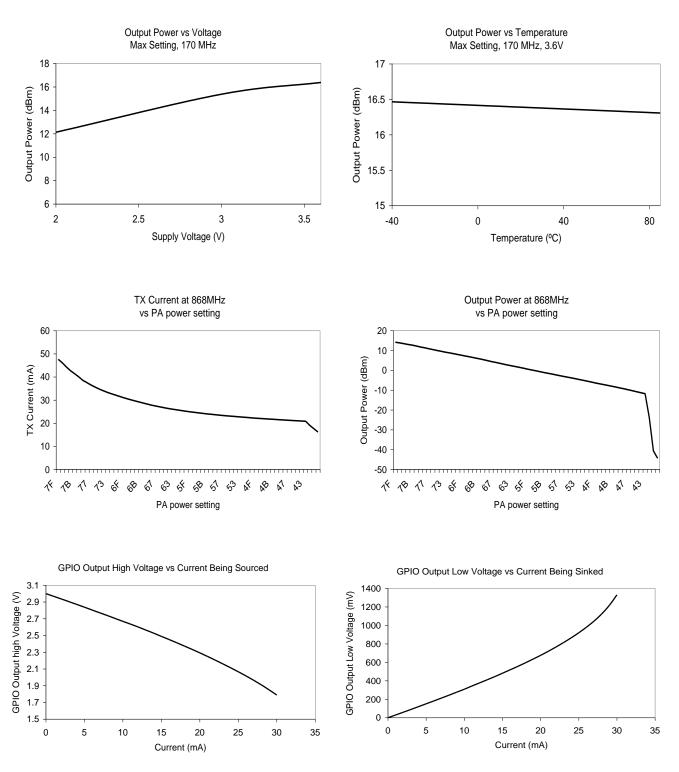
The **CC1200** can be configured to provide a voltage proportional to temperature on GPIO1. Using the information above, the temperature can be estimated by measuring this voltage. Please refer to the **CC120X** user guide for more information.





## 2 Typical Performance Curves

 $T_A = 25^{\circ}C, VDD = 3.0 V$ 





# 3 Pin Configuration

The **CC1200** pin-out is shown in the table below.

Pin #	Pin name	Type / direction	Description
1	VDD_GUARD	Power	2.0 - 3.6 V VDD
2	RESET_N	Digital Input	Asynchronous, active-low digital reset
3	GPIO3	Digital Input/Output	General purpose IO
4	GPIO2	Digital Input/Output	General purpose IO
5	DVDD	Power	2.0 - 3.6 VDD to internal digital regulator
6	DCPL	Power	Digital regulator output to external decoupling capacitor
7	SI	Digital Input	Serial data in
8	SCLK	Digital Input	Serial data clock
9	SO(GPIO1)	Digital Input/Output	Serial data out (General purpose IO)
10	GPIO0	Digital Input/Output	General purpose IO
11	CSn	Digital Input	Active-low chip-select
12	DVDD	Power	2.0 - 3.6 V VDD
13	AVDD_IF	Power	2.0 - 3.6 V VDD
14	RBIAS	Analog	External high precision R
15	AVDD_RF	Power	2.0 - 3.6 V VDD
16	N.C.		Not connected
17	PA	Analog	Single-ended TX output
18	TRX_SW	Analog	TX/RX switch. Connected internally to GND in TX and floating (high-impedance) in RX.
19	LNA_P	Analog	Differential RX input
20	LNA_N	Analog	Differential RX input
21	DCPL_VCO	Power	Pin for external decoupling of VCO supply regulator
22	AVDD_SYNTH1	Power	2.0 - 3.6 V VDD
23	LPF0	Analog	External loopfilter components
24	LPF1	Analog	External loopfilter components
25	AVDD_PFD_CHP	Power	2.0 - 3.6 V VDD
26	DCPL_PFD_CHP	Power	Pin for external decoupling of PFD and CHP regulator
27	AVDD_SYNTH2	Power	2.0 - 3.6 V VDD
28	AVDD_XOSC	Power	2.0 - 3.6 V VDD
29	DCPL_XOSC	Power	Pin for external decoupling of XOSC supply regulator
30	XOSC_Q1	Analog	Crystal oscillator pin 1 (must be grounded if a TCXO or other external clock connected to EXT_XOSC is used)
31	XOSC_Q2	Analog	Crystal oscillator pin 2 (must be left floating if a TCXO or other external clock connected to EXT_XOSC is used)
32	EXT_XOSC	Digital Input	Pin for external XOSC input (must be grounded if a regular XOSC connected to XOSC_Q1 and XOSC_Q2 is used)
-	GND	Ground Pad	The ground pad must be connected to a solid ground plane



## 4 Block Diagram

A system block diagram of **CC1200** is shown Figure 4.1.

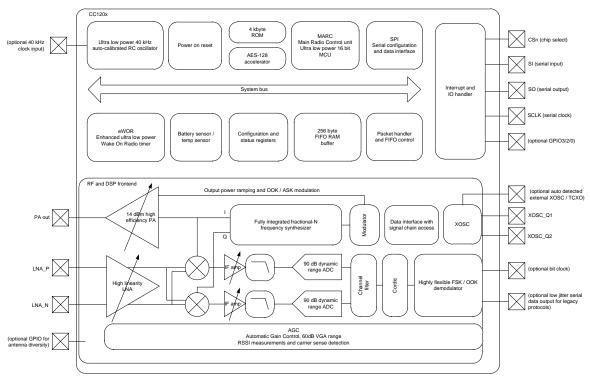


Figure 4.1 : System Block Diagram

### 4.1 Frequency Synthesizer

At the heart of **CC1200** there is a fully integrated, fractional-N, ultra high performance frequency synthesizer. The frequency synthesizer is designed for excellent phase noise performance, providing very high selectivity and blocking performance. The system is designed to comply with the most stringent regulatory spectral masks at maximum transmit power.

Either a crystal can be connected to XOSC\_Q1 and XOSC\_Q2, or a TCXO can be connected to the EXT\_XOSC input. The oscillator generates the reference frequency for the synthesizer, as well as clocks for the ADC and the digital part. To reduce system cost, **CC1200** has high accuracy frequency estimation and compensation registers to measure and compensate for crystal inaccuracies, enabling the use of lower cost crystals. If a TCXO is used, the **CC1200** will automatically turn the TCXO on and off when needed to support low power modes and Wake-On-Radio operation.

### 4.2 Receiver

**CC1200** features a highly flexible receiver. The received RF signal is amplified by the low-noise amplifier (LNA) and down-converted in quadrature (I and Q) to the intermediate frequency (IF). At IF, the I/Q signals are digitized by the high dynamic range ADCs.

An advanced Automatic Gain Control (AGC) unit adjusts the front end gain, and enables the **CC1200** to receive both strong and weak signals, even in the presence of strong interferers. High attenuation channel and data filtering enable reception with strong neighbor channel interferers. The I/Q signal is converted to a phase / magnitude signal to support both FSK and OOK modulation schemes.

A sophisticated pattern recognition algorithm locks onto the synchronization word without need for preamble settling bytes. Receiver settling time is therefore reduced to the settling time of the AGC, typically 4 bits. The advanced pattern recognition also greatly reduces the problem of false sync triggering on noise, further reducing power consumption and improving sensitivity and reliability.



The pattern recognition logic can also be used as a high performance preamble detector to reliably detect a valid preamble in the channel.

A novel I/Q compensation algorithm removes any problem of I/Q mismatch and hence avoids time consuming and costly I/Q / image calibration steps in production or in the field.

### 4.3 Transmitter

The **CC1200** transmitter is based on direct synthesis of the RF frequency (in-loop modulation). To achieve effective spectrum usage, **CC1200** has extensive data filtering and shaping in TX to support high throughput data communication in narrowband channels. The modulator also controls power ramping to remove issues such as spectral splattering when driving external high power RF amplifiers.

### 4.4 Radio Control and User Interface

The **CC1200** digital control system is built around MARC (Main Radio Control) implemented using an internal high performance 16 bit ultra low power processor. MARC handles power modes, radio sequencing and protocol timing.

A 4-wire SPI serial interface is used for configuration and data buffer access. The digital baseband includes support for channel configuration, packet handling, and data buffering. The host MCU can stay in power down until a valid RF packet has been received, and then burst read the data, greatly reducing the power consumption and computing power required from the host MCU.

The **CC1200** radio control and user interface is based on the widely used **CC1101** transceiver to enable easy SW transition between the two platforms. The command strobes and the main radio states are the same for the two platforms.

For legacy formats **CC1200** also has support for two serial modes. In synchronous serial mode **CC1200** performs bit synchronization and provides the MCU with a bit clock with associated data. In transparent mode **CC1200** outputs the digital baseband signal using a digital interpolation filter to eliminate jitter introduced by digital filtering and demodulation.

### 4.5 Enhanced Wake-On-Radio (eWOR)

eWOR, using a flexible integrated sleep timer, enables automatic receiver polling with no intervention from the MCU. The **CC1200** will enter RX, listen and return to sleep if a valid RF packet is not received. The sleep interval and duty cycle can be configured to make a trade-off between network latency and power consumption. Incoming messages are time-stamped to simplify timer re-synchronization.

The eWOR timer runs off an ultra low power 32 kHz RC oscillator. To improve timing accuracy, the RC oscillator can be automatically calibrated to the RF crystal in configurable intervals.

### 4.6 Sniff Mode

The **CC1200** supports very quick start up times, and requires very few preamble bits. Sniff Mode uses this to dramatically reduce the current consumption while the receiver is waiting for data.

Since the **CC1200** is able to wake up and settle much faster than the length of most preambles, it is not required to be in RX continuously while waiting for a packet to arrive. Instead, the enhanced wake-on-radio feature can be used to put the device into sleep periodically. By setting an appropriate sleep time, the **CC1200** will be able to wake up and receive the packet when it arrives with no performance loss. This removes the need for accurate timing synchronization between transmitter and receiver, and allows the user to trade off current consumption between the transmitter and receiver.

### 4.7 Antenna Diversity

Antenna diversity can increase performance in a multi-path environment. An external antenna switch is required. The switch can be automatically controlled by **CC1200** using one of the GPIO pins (also support for differential output control signal typically used in RF switches).



If antenna diversity is enabled, the GPIO will alternate between high and low states until a valid RF input signal is detected. An optional acknowledge packet can be transmitted without changing GPIO state.

An incoming RF signal can be validated by received signal strength, by using the automatic preamble detector, or a combination of the two. Using the preamble detector will make a more robust system and avoid the need to set a defined signal strength threshold, as this threshold will set the sensitivity limit of the system.



**CC1200** 

## **5** Typical Application Circuit

Very few external components are required for the operation of **CC1200**. A typical application circuit is shown below. Note that it does not show how the board layout should be done, which will greatly influence the RF performance of **CC1200**.

This section is meant as an introduction only. Note that decoupling capacitors for power pins are not shown in the figure below.

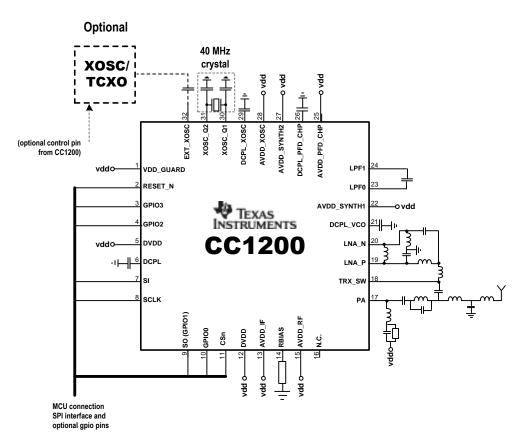


Figure 5.1 : Typical Application Circuit



15-Jun-2013

## **PACKAGING INFORMATION**

Γ	Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
		(1)		Drawing		Qty	(2)		(3)		(4/5)	
	CC1200RHBR	PREVIEW	QFN	RHB	32	3000	Green (RoHS & no Sb/Br)	CU NIPDAUAG	Level-3-260C-168 HR	-40 to 85	CC1200	
	CC1200RHBT	PREVIEW	QFN	RHB	32	250	Green (RoHS & no Sb/Br)	CU NIPDAUAG	Level-3-260C-168 HR	-40 to 85	CC1200	

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW**: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

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the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

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NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. QFN (Quad Flatpack No-Lead) Package configuration.
- D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- F. Falls within JEDEC MO-220.



## RHB (S-PVQFN-N32)

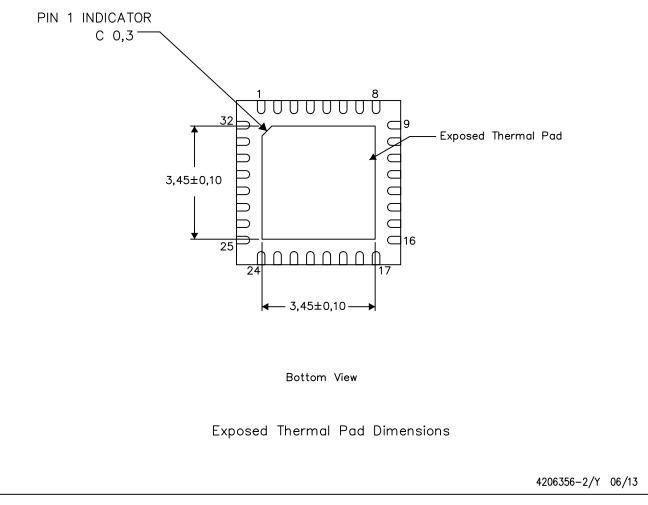
## PLASTIC QUAD FLATPACK NO-LEAD

### THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.

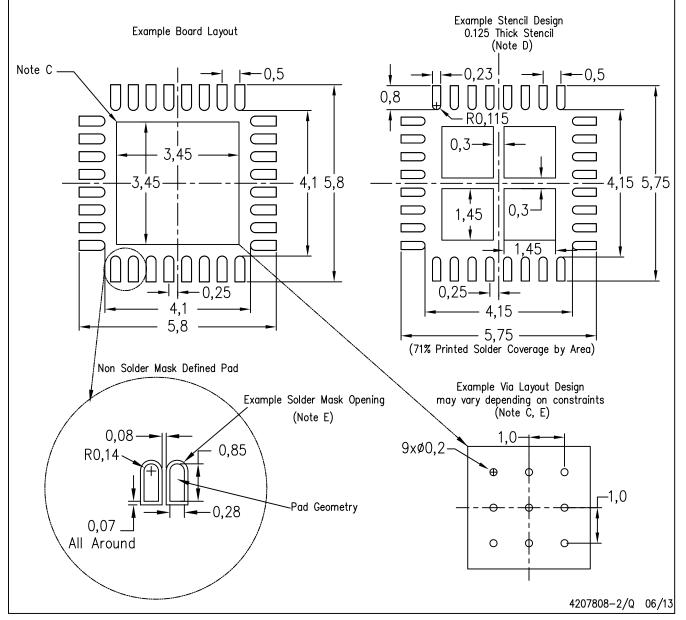


### NOTE: A. All linear dimensions are in millimeters



# RHB (S-PVQFN-N32)

# PLASTIC QUAD FLATPACK NO-LEAD



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat—Pack Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <http://www.ti.com>.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- E. Customers should contact their board fabrication site for recommended solder mask tolerances and via tenting recommendations for vias placed in the thermal pad.



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